

(19) United States

(12) Patent Application Publication (10) Pub. No.: US 2020/0159115 A1 Ono et al.

May 21, 2020 (43) **Pub. Date:**

(54)	NOVEL SALT COMPOUND, CHEMICALLY
	AMPLIFIED RESIST COMPOSITION, AND
	PATTERNING PROCESS

(71) Applicant: Shin-Etsu Chemical Co., Ltd., Tokyo

(JP)

(72) Inventors: Emiko Ono, Joetsu-shi (JP);

Masayoshi Sagehashi, Joetsu-shi (JP); Masahiro Fukushima, Joetsu-shi (JP);

Yuki Kera, Joetsu-shi (JP)

(73) Assignee: Shin-Etsu Chemical Co., Ltd., Tokyo

(JP)

(21) Appl. No.: 16/669,780

(22)Filed: Oct. 31, 2019

(30)Foreign Application Priority Data

Nov. 15, 2018 (JP) 2018-214718

Publication Classification

(51) Int. Cl. G03F 7/004 G03F 7/039 (2006.01)(2006.01)

G03F 7/038	(2006.01)
C07D 307/77	(2006.01)
C07C 381/12	(2006.01)
C07C 309/12	(2006.01)
C07D 311/00	(2006.01)
C07D 333/76	(2006.01)
C07D 333/08	(2006.01)
C07D 327/06	(2006.01)
C08F 220/18	(2006.01)

(52) U.S. Cl.

CPC G03F 7/0045 (2013.01); G03F 7/0397 (2013.01); G03F 7/0382 (2013.01); C07D **307/77** (2013.01); **C07C 381/12** (2013.01); G03F 7/162 (2013.01); C07D 311/00 (2013.01); CO7D 333/76 (2013.01); CO7D 333/08 (2013.01); C07D 327/06 (2013.01); C08F 220/18 (2013.01); C07C 309/12 (2013.01)

(57)**ABSTRACT**

A novel salt having an amide bond in its anion structure is provided. A chemically amplified resist composition comprising the salt has advantages including minimal defects and improved values of sensitivity, LWR, MEF and CDU, when processed by lithography using high-energy radiation such as KrF excimer laser, ArF excimer laser, EB or EUV.